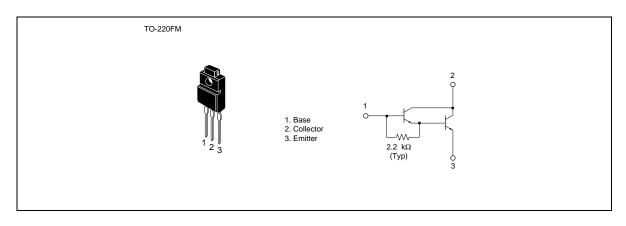
Silicon NPN Triple Diffused

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Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

m Symbo		Rating	Unit	
Collector to base voltage	V _{cbo}	60	V	
Collector to emitter voltage	V _{ceo}	60	V	
Emitter to base voltage	V _{ebo}	7	V	
Collector current	I _c	8	А	
Collector peak current	Ⅰ _{C(peak)}	12	А	
Collector power dissipation	P _c	2	W	
	P _c * ¹	25		
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

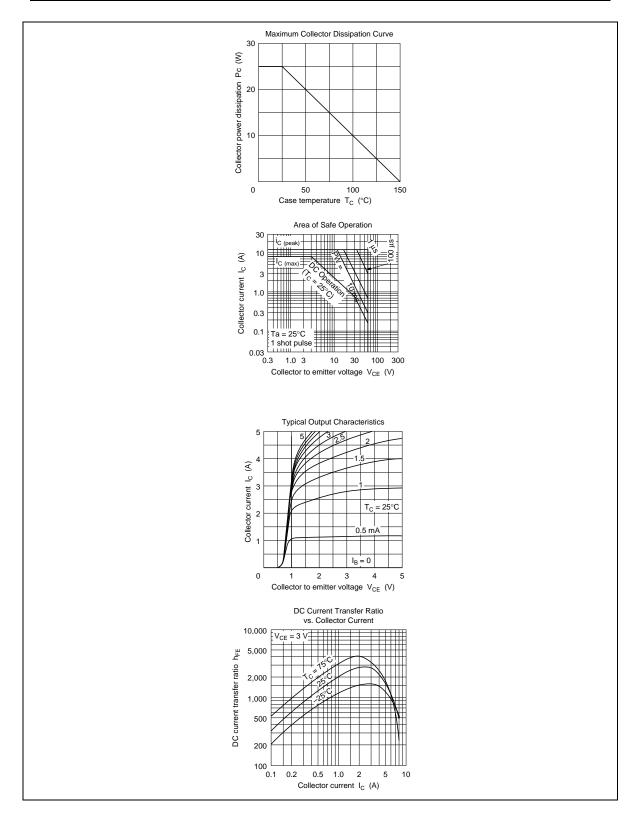
Note: 1. Value at $T_c = 25^{\circ}C$.

Electrical Characteristics ($Ta = 25^{\circ}C$)

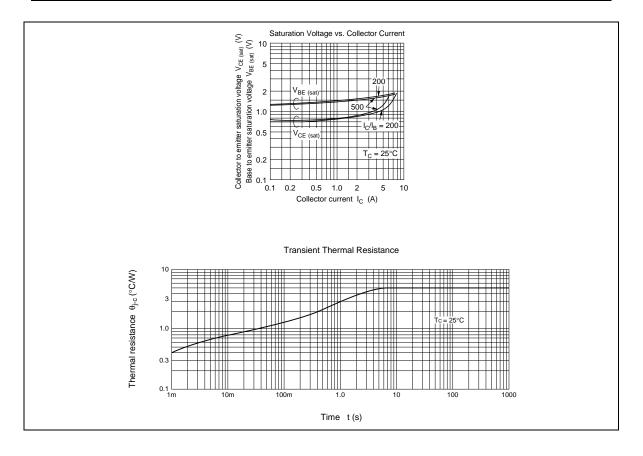
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	_		V	$I_{c} = 0.1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\scriptscriptstyle (BR)CEO}$	60	_	—	V	$I_c = 25 \text{ mA}, \text{ R}_{_{BE}} = \infty$
Emitter to base breakdown voltage	$V_{\scriptscriptstyle (BR)EBO}$	7	—	_	V	$I_{\rm e} = 50$ mA, $I_{\rm c} = 0$
Collector cutoff current	I _{cbo}	_	_	10	μA	$V_{_{CB}} = 50 \text{ V}, \text{ I}_{_{E}} = 0$
	I _{ceo}	_	_	10	_	$V_{\rm CE}$ = 50 V, $R_{\rm BE}$ = ∞
DC current transfer ratio	h _{FE}	1000	_	20000		$V_{ce} = 3 V, I_c = 4 A^{*1}$
Collector to emitter saturation	$V_{\scriptscriptstyle CE(sat)1}$	_	_	1.5	V	$I_{c} = 4 \text{ A}, I_{B} = 8 \text{ mA}^{*1}$
voltage	I _{CE(sat)2}	_	_	3.0	_	$I_{c} = 8 \text{ A}, I_{B} = 80 \text{ mA}^{*1}$
Base to emitter saturation	$V_{\scriptscriptstyle BE(sat)1}$	_	_	2.0	V	$I_{c} = 4 \text{ A}, I_{B} = 8 \text{ mA}^{*1}$
	$V_{\scriptscriptstyle BE(sat)2}$	_		3.5		$I_{c} = 8 \text{ A}, I_{B} = 80 \text{ mA}^{*1}$

Note: 1. Pulse test.

See switching characteristic curve of 2SD1572.



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